

FILM FORMATION METHOD AND FILM FORMATION APPARATUS

FILM FORMATION METHOD AND FILM FORMATION APPARATUS

Patent Number: JP5206036

Publication date: 1993-08-13

Inventor(s): AOYANAGI KATSUNOBU; others: 02

Applicant(s): RIKAGAKU KENKYUSHO

Requested Patent: JP5206036

Application Number: JP19920014991 19920130

Priority Number(s):

IPC Classification: H01L21/205

EC Classification:

EC Classification:

Equivalents: JP3126787B2

Abstract

PURPOSE: To make it possible to form a thin film having an excellent in-plane uniformity, ALE condition, crystal quality, acute steepness of heterointerface, and others without damaging a substrate.

CONSTITUTION: A substrate 3 is arranged in a vacuum chamber 1 which is evacuated at a given degree of vacuum and heated. At the same time, with a gas ejection mechanism having a nozzle 6 arranged toward the substrate 3, and a high-speed switching valve 8 which provided near the nozzle 6, a material gas is ejected to the substrate 3 intermittently or continuously to grow crystals on the surface of the substrate 3 for the formation of a film.